





## **SBR230LS SCHOTTKY RECTIFIER**



#### **Features**

- 125°C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- · High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

### Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	30	V
Average Rectified Forward Current @T <sub>L</sub> = 105°C	lo	2	Α
Peak Repetitive Forward Current (at rated $V_R$ , square wave, 100kHz, $T_L$ =95°C)	I <sub>FRM</sub>	4.0	Α
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Half-wave, Single Phase, 60 Hz)	I <sub>FSM</sub>	25	Α
Operating Junction Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C
Voltage Rate of Change (rated V <sub>R</sub> , T <sub>J</sub> =25°C)	dv/dt	10000	V/µs

Characteristic	Symbol	Тур.	Max.	Units
Forward Voltage $@I_F = 1A, T_A = 25^{\circ}C$ $@I_F = 2A, T_A = 25^{\circ}C$ $@I_F = 1A, T_A = 100^{\circ}C$ $@I_F = 2A, T_A = 100^{\circ}C$	V <sub>FM</sub>	0.42 0.50 0.33 0.45	0.60 0.75 0.52 0.67	V
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 100°C	I <sub>RM</sub>	0.03 10	1.0 25	mA
Junction Capacitance (Note 1)	Cj	80	150	pF

Note 1. Measured at 1MHz and applied reverse voltage of 5.0V D.C.

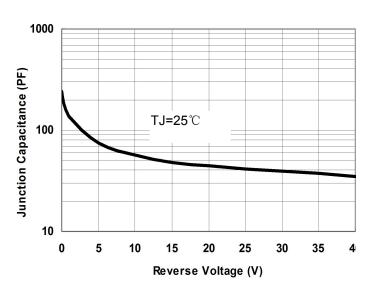
- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •







## **Ratings and Characteristics Curves**



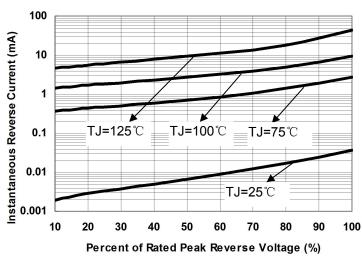


Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics

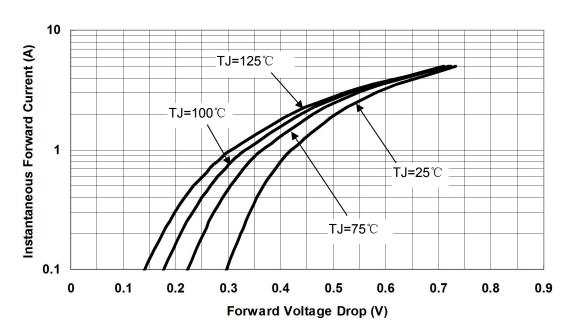


Fig.3-Typical Forward Voltage Drop Characteristics

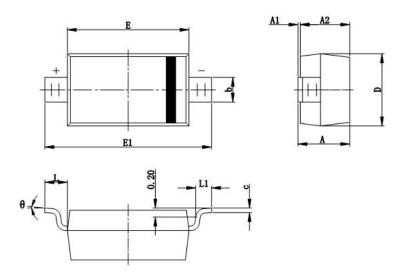
<sup>•</sup> http://www.smc-diodes.com - sales@ smc-diodes.com •







### **Mechanical Dimensions SOD-123**



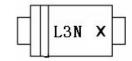
OVMDOL	Millimeters		Inches	
SYMBOL	MIN.	MAX.	MIN.	MAX.
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
С	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
Е	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500	REF.	0.020	REF.
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

## **Ordering Information**

Device	Package	Shipping
SBR230LS	SOD-123 (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Marking Diagram**

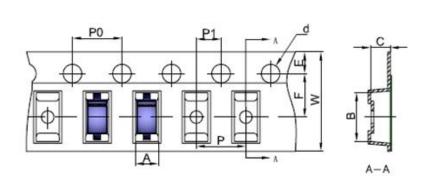


Where X is Date Code

L3N = Part Name

SBR230LS

# **Carrier Tape Specification SOD-123**



SYMBOL	Millimeters		
STWIBUL	Min.	Max.	
Α	1.80	1.90	
В	3.89	3.99	
С	1.52	1.62	
d	1.45	1.65	
E	1.65	1.85	
F	3.40	3.60	
Р	3.90	4.10	
P0	3.90	4.10	
P1	1.90	2.10	
W	7.90	8.30	

- China Germany Korea Singapore United States
  - http://www.smc-diodes.com sales@ smc-diodes.com •







#### DISCLAIMER:

- 1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the SMC Sangdest Microelectronics (Nanjing) Co., Ltd sales department for the latest version of the datasheet(s).
- 2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.
- 3- In no event shall SMC Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). SMC Sangdest Microelectronics (Nanjing) Co., Ltd assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.
- 4- In no event shall SMC Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.
- 5- No license is granted by the datasheet(s) under any patents or other rights of any third party or SMC Sangdest Microelectronics (Nanjing) Co., Ltd.
- 6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of SMC Sangdest Microelectronics (Nanjing) Co., Ltd.
- 7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations..